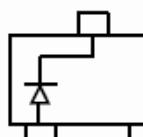


SCHOTTKY DIODE

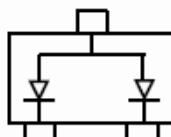
FEATURES

- Low Forward Voltage
- Fast Switching

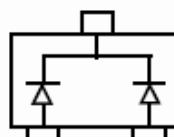
MARKING



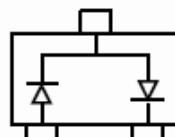
BAS40: B1



BAS40-06: L2



BAS40-05: 45



BAS40-04: CB



MAXIMUM RATINGS (TA=25°C unless otherwise noted)

Parameter	Symbol	Limits	Unit
Peak repetitive peak reverse voltage	V _{RRM}		
Working peak reverse voltage	V _{RWM}	40	V
Forward continuous Current	I _{FM}	200	mA
Power Dissipation	P _D	200	mW
Thermal Resistance. Junction to Ambient Air	R _{JA}	625	°C/W
Junction temperature	T _J	125	°C
Storage temperature range	T _{STG}	-65-125	°C

Electrical Ratings @TA=25°C

Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	V _(BR)	I _R = 10µA	40		V
Reverse voltage leakage current	I _R	V _R =30V		200	nA
Forward voltage	V _F	I _F =1mA I _F =40mA		380 1000	mV
Diode capacitance	C _D	V _R =0,f=1MHz		5	pF
Reverse Recovery time	t _{rr}	I _{rr} =1mA, I _R =I _F =10mA R _L =100		5	nS

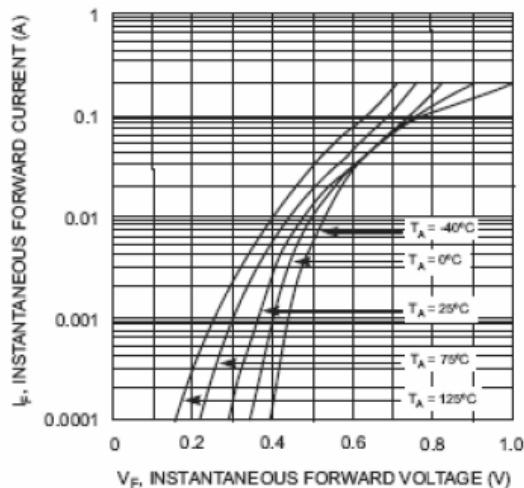
BAS40/-04/-05/-06 Typical Characteristics


Fig. 1 Typical Forward Voltage

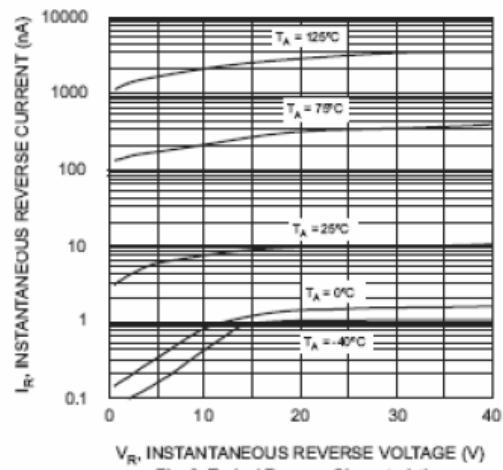


Fig. 2 Typical Reverse Characteristics

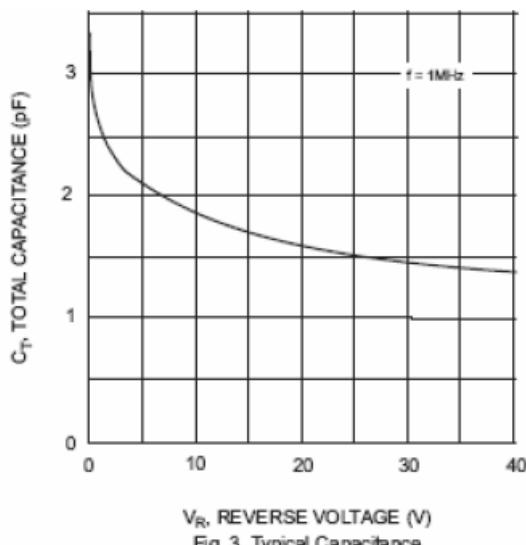


Fig. 3 Typical Capacitance

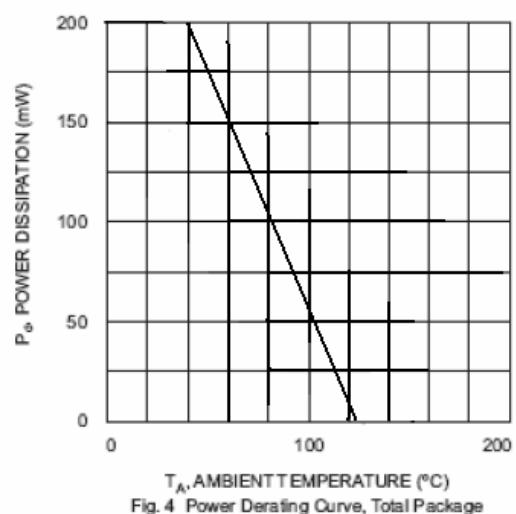


Fig. 4 Power Derating Curve, Total Package